

RoHS

COMPLIANT HALOGEN

FREE Available

Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

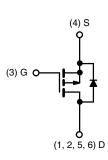
| PRODUCT SUMMARY | | | | | | |
|---------------------|------------------------------------|--------------------|-----------------------|--|--|--|
| V _{DS} (V) | R_{DS(on)} (Ω) | I _D (A) | Q _g (Typ.) | | | |
| | 0.023 at V_{GS} = - 4.5 V | - 7.9 | | | | |
| - 12 | 0.029 at V_{GS} = - 2.5 V | - 7.0 | 22 | | | |
| | 0.041 at V _{GS} = - 1.8 V | - 5.9 | | | | |

FEATURES

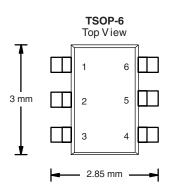
- Halogen free According to IEC61249-2-21
 Definition
- TrenchFET[®] Power MOSFET: 1.8 V Rated
- Ultra-Low On-Resistance
- Compliant to RoHs Directive 2002/95/EC

APPLICATIONS

- · Load Switch
- PA Switch



P-Channel MOSFET



Ordering Information: Si3473DV-T1-E3 (Lead (Pb)-free) Si3473DV-T1-GE3 (Lead (Pb)-free and Halogen free) Marking Code: 73xxx

| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | | | |
|--|-----------------------------------|------------------|--------------|-------|----|--|
| Parameter | Symbol | 5 s | Steady State | Unit | | |
| Drain-Source Voltage | V _{DS} | - 12 | | V | | |
| Gate-Source Voltage | V _{GS} | ± 8 | | | | |
| | T _A = 25 °C | - I _D | - 7.9 | - 5.9 | • | |
| Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$ | T _A = 85 °C | | - 5.7 | - 4.3 | | |
| Pulsed Drain Current | | I _{DM} | - 20 | | A | |
| Continuous Source Current (Diode Conduction) ^a | ۱ _s | - 1.7 | - 0.9 | | | |
| | T _A = 25 °C | Р | 2.0 | 1.1 | w | |
| Maximum Power Dissipation ^a | T _A = 85 °C | P _D | 1.0 | 0.6 | vv | |
| Operating Junction and Storage Temperature Ran | T _J , T _{stg} | - 55 to 150 | | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| | t ≤ 5 s | R _{thJA} | 45 | 62.5 | | |
| Maximum Junction-to-Ambient ^a | Steady State | ' 'thJA | 90 | 110 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R _{thJF} | 25 | 30 | | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|---------------------|---|------|-------|-------|------|--|
| Static | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \mu A$ - (| | | - 1 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 8 V$ | | | ± 100 | nA | |
| | | V _{DS} = - 12 V, V _{GS} = 0 V | | | - 1 | μA | |
| Zero Gate Voltage Drain Current | IDSS | V_{DS} = - 12 V, V_{GS} = 0 V, T_{J} = 85 °C | | | - 5 | | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} = - 5 V, V _{GS} = - 4.5 V | - 20 | | | А | |
| | R _{DS(on)} | V _{GS} = - 4.5 V, I _D = - 7.9 A | | 0.019 | 0.023 | Ω | |
| Drain-Source On-State Resistance ^a | | V _{GS} = - 2.5 V, I _D = - 7.0 A | | 0.024 | 0.029 | | |
| | | V _{GS} = - 1.8 V, I _D = - 3 A | | 0.033 | 0.041 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = - 5 V, I _D = - 7.9 A | | 28 | | S | |
| Diode Forward Voltage ^a | V _{SD} | I _S = - 1.7 A, V _{GS} = 0 V | | - 0.7 | - 1.2 | V | |
| Dynamic ^b | | - | | | | | |
| Total Gate Charge | Qg | | | 22 | 33 | | |
| Gate-Source Charge | Q _{gs} | V_{DS} = - 6 V, V_{GS} = - 4.5 V, I_D = - 7.9 A | | 3.2 | | nC | |
| Gate-Drain Charge | Q _{gd} | | | 5.8 | | | |
| Turn-On Delay Time | t _{d(on)} | | | 25 | 40 | | |
| Rise Time | t _r | V_{DD} = - 6 V, R_L = 6 Ω | | 50 | 75 | ns | |
| Turn-Off Delay Time | t _{d(off)} | ${\rm I}_{\rm D}\cong$ - 1 A, ${\rm V}_{\rm GEN}$ = - 4.5 V, ${\rm R}_{\rm g}$ = 6 Ω | | 130 | 200 | | |
| Fall Time | t _f | | | 110 | 165 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = - 1.7 A, dl/dt = 100 A/μs | | 65 | 90 | | |

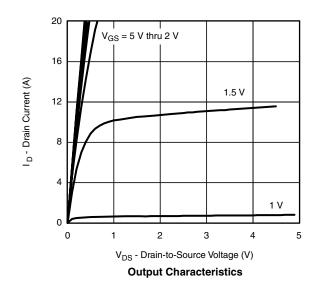
Notes:

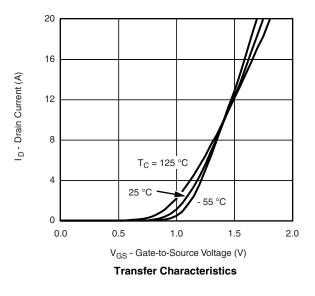
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



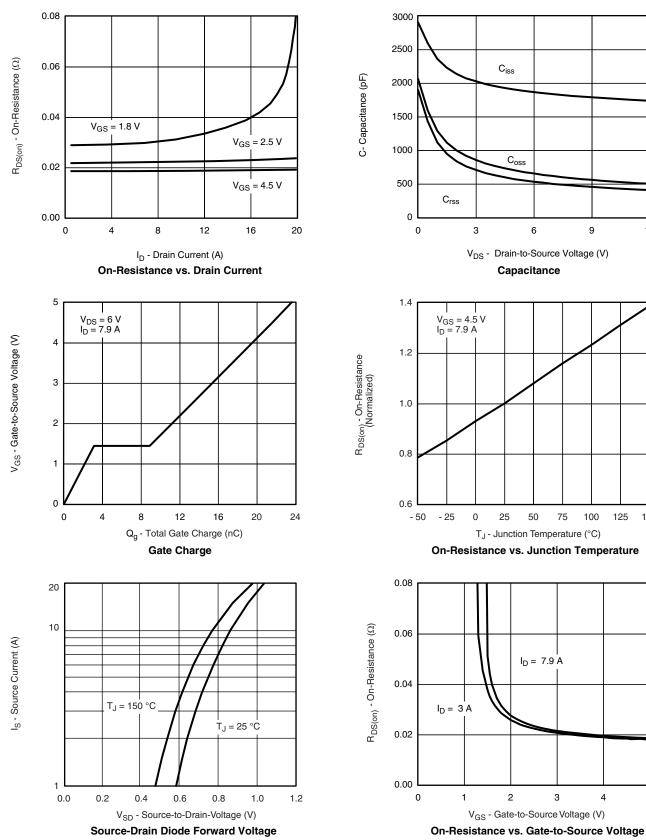




Si3473DV

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

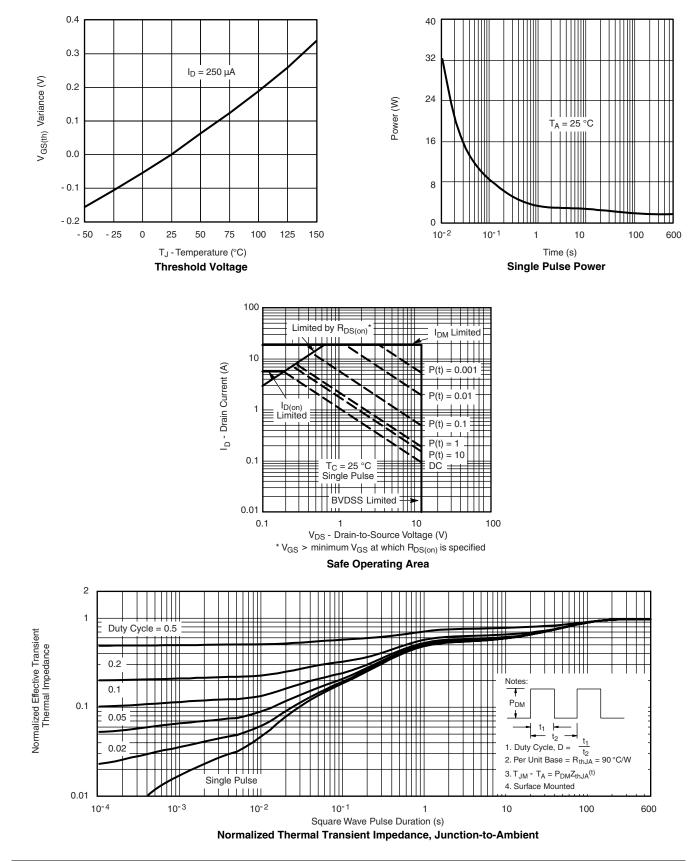


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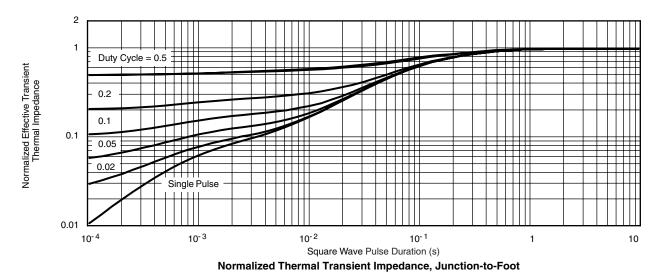
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Si3473DV Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg271937.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



| | MIL | LIMETER | RS | INCHES | | | |
|---|----------|---------|------|------------|-----------|-------|--|
| Dim | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.91 | - | 1.10 | 0.036 | - | 0.043 | |
| A ₁ | 0.01 | - | 0.10 | 0.0004 | - | 0.004 | |
| A ₂ | 0.90 | - | 1.00 | 0.035 | 0.038 | 0.039 | |
| b | 0.30 | 0.32 | 0.45 | 0.012 | 0.013 | 0.018 | |
| С | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 | |
| D | 2.95 | 3.05 | 3.10 | 0.116 | 0.120 | 0.122 | |
| Е | 2.70 | 2.85 | 2.98 | 0.106 | 0.112 | 0.117 | |
| E ₁ | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 | |
| е | 0.95 BSC | | | 0.0374 BSC | | | |
| e ₁ | 1.80 | 1.90 | 2.00 | 0.071 | 0.075 | 0.079 | |
| L | 0.32 | - | 0.50 | 0.012 | - | 0.020 | |
| L ₁ | 0.60 Ref | | | | 0.024 Ref | | |
| L ₂ | 0.25 BSC | | | | 0.010 BSC | | |
| R | 0.10 | - | - | 0.004 | - | - | |
| θ | 0° | 4° | 8° | 0° | 4° | 8° | |
| θ_1 | 7° Nom | | | | 7° Nom | | |
| ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540 | | | | | | | |

PAD Pattern



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Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

| ECN: C22-0860-Rev. B, 24-Oct-2022 | |
|-----------------------------------|--|
| DWG: 3010 | |

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